

# RD3CYDT08

### **IGBT** Driver

REJ03D0905-0300 Rev.3.00 Apr 22, 2008

### **Description**

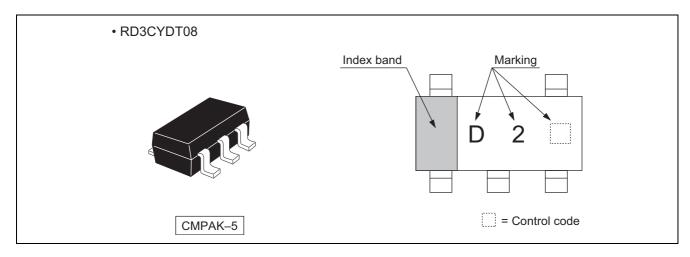
The RD3CYDT08 has two-input AND gate in a 5 pin package. This product is suited as IGBT Driver IC for the strobe.

#### **Features**

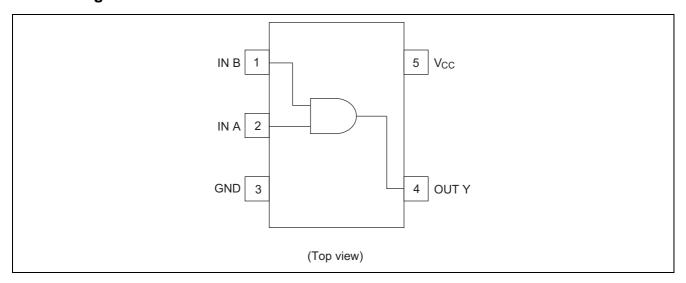
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range: 2.0 to 3.6 V
- Operating temperature range : -40 to +85°C
- High drive current
  - $I_{OH}$  short = -130 mA (typ) (@V<sub>CC</sub> = 3.3 V)
- Low sink current
  - $I_{OL}$  short = 45 mA (typ) (@ $V_{CC}$  = 3.3 V)
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
RD3CYDT08CME	CMPAK-5 pin	PTSP0005ZC-A (CMPAK-5V)	СМ	E (3,000 pcs/reel)

#### **Outline and Article Indication**



## **Pin Arrangement**



## **Logic Diagram**

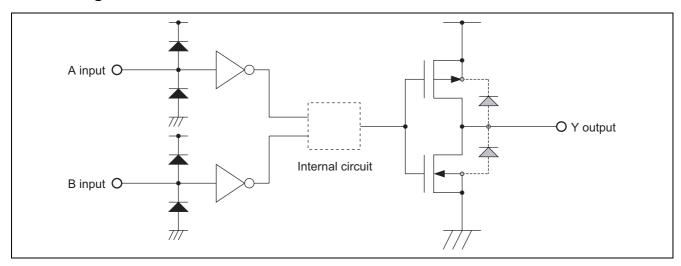


### **Function Table**

Inp	Output Y	
Α	В	Output 1
L	L	L
Н	L	L
L	Н	L
Н	Н	Н

H : High level L : Low level

## **Block Diagram**



### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	-0.5 to 4.6	V	
Input voltage range *1	VI	$-0.5$ to $V_{CC} + 0.5$	V	
Output voltage range *1, 2	Vo	$-0.5$ to $V_{CC} + 0.5$	V	
Input clamp current	I <sub>IK</sub>	±50	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I <sub>OK</sub>	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	Io	-200	mA	V <sub>O</sub> = 0
Continuous output current		100	IIIA	$V_O = V_{CC}$
Continuous current through V <sub>CC</sub> or GND	I <sub>CC</sub> or I <sub>GND</sub>	±200	mA	
Maximum power dissipation at Ta = $25^{\circ}$ C (in still air) * <sup>3</sup>	P <sub>T</sub>	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed. When Over shoot / Under shoot pulse width is under 10 ns, input and output voltage permit to -1.5 V or V<sub>CC</sub>+1.5V.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

### **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V <sub>CC</sub>	2.0	3.6	V	
Input voltage range	VI	0	V <sub>CC</sub>	V	
Output voltage range	Vo	0	V <sub>CC</sub>	V	
Input transition rise or fall rate	Δt / ΔV	0	100	ns / V	
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

#### **Electrical Characteristic**

 $Ta = -40 \text{ to } 85^{\circ}\text{C}$ 

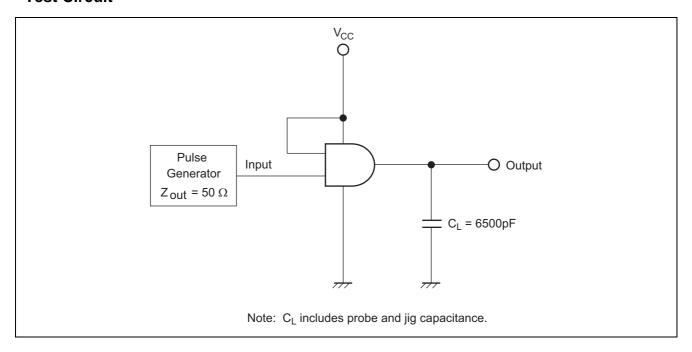
Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test condition
Innut voltogo	$V_{IH}$	3.0 to 3.6	1.4	_	1	V	
Input voltage	$V_{IL}$	3.0 to 3.6	_	_	0.5	\ \	
Output current	I <sub>OH</sub> short	3.3	-100	-130	-160	mA	
	I <sub>OL</sub> short	3.3	30	45	60	IIIA	
Input current	I <sub>IN</sub>	3.6	_	_	±5	μΑ	$V_{IN} = 3.6 \text{ V or GND}$
Quiescent	1	3.6			10		$V_{IN} = V_{CC}$ or GND,
supply current	I <sub>CC</sub>	3.0		_	10	μΑ	$I_{O} = 0$
Input capacitance	C <sub>IN</sub>	3.3		2.5		pF	$V_{IN} = V_{CC}$ or GND

## **Switching Characteristics**

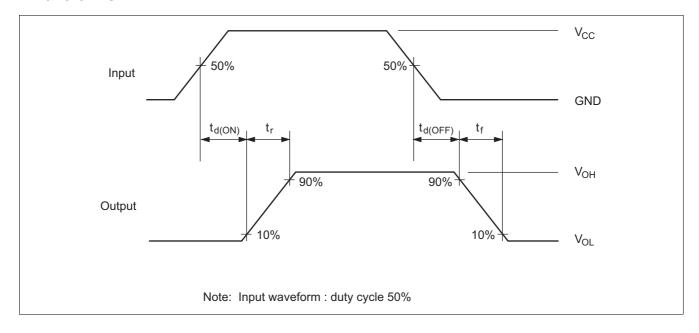
 $V_{CC}=3.3\pm0.3\ V$ 

Item	Symbol	Ta = -40 to 85°C			Unit	Test	FROM	TO
item	Symbol	Min	Тур	Max	Ollic	Conditions	(Input)	(Output)
Dropogation dolay time	t <sub>d(ON)</sub>	_	_	50				
Propagation delay time	t <sub>d(OFF)</sub>	_	_	160		$C_1 = 6500 \text{ pF}$	A or D	V
Output rise time	t <sub>r</sub>	_	_	500	ns	C <sub>L</sub> = 6500 pr	A or B	r
Output fall time	t <sub>f</sub>	_	_	1500				

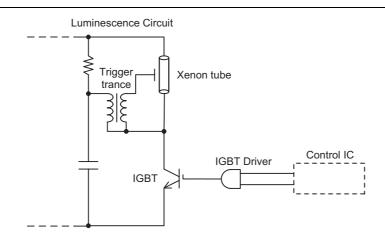
### **Test Circuit**



## Waveforms



## **Application Note (Strobe circuit)**



#### Combination example

SYSTEM	IGBT	IGBT Driver	Control IC
3.3 V	RJP4002ANS RJP4002ASA	RD3CYD08 RD3CYDT08	- 3.3 V signal
5.0 V	RJP4003ANS RJP4003ASA	RD5CYD08 RD5CYDT08	<ul><li>5.0 V signal</li><li>3.3 V signal</li></ul>

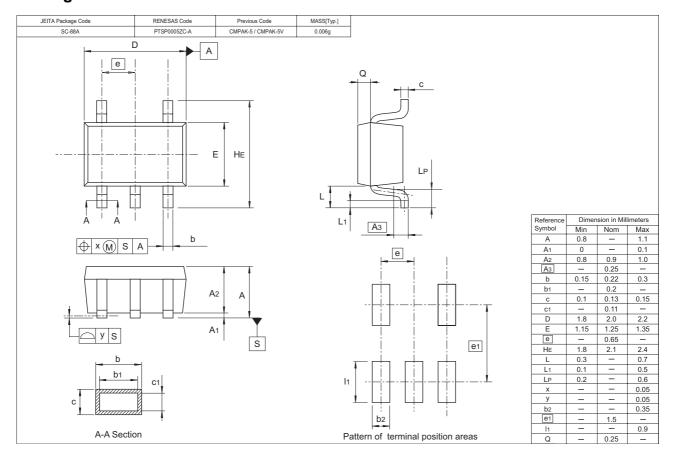
### **IGBT** Driver Lineup

TYPE No.	Specification	Package	
RD3CYD08	$V_{CC}$ = 2.0 to 3.6V CMOS lever input $I_{OH}(short)$ = -130mA(typ) @ $V_{CC}$ = 3.3V $I_{OL}(short)$ = 45mA(typ) @ $V_{CC}$ = 3.3V	CMPAK-5 VSON-5	
RD3CYDT08	$V_{CC}$ = 2.0 to 3.6V CMOS lever input $I_{OH}(short)$ = -130mA(typ) @ $V_{CC}$ = 3.3V $I_{OL}(short)$ = 45mA(typ) @ $V_{CC}$ = 3.3V	CMPAK-5	
RD5CYD08	$V_{CC} = 4.0 \text{ to } 6.0 \text{V CMOS lever input}$ $I_{OH}(\text{short}) = -130 \text{mA(typ)} @ V_{CC} = 5.0 \text{V}$ $I_{OL}(\text{short}) = 40 \text{mA(typ)} @ V_{CC} = 5.0 \text{V}$	CMPAK 5	
RD5CYDT08	$V_{CC} = 4.0 \text{ to } 6.0 \text{V TTL lever input}$ $I_{OH}(\text{short}) = -130 \text{mA(typ)} @ V_{CC} = 5.0 \text{V}$ $I_{OL}(\text{short}) = 40 \text{mA(typ)} @ V_{CC} = 5.0 \text{V}$	CMPAK-5	

#### **IGBT Lineup**

TYPE No.	Specification	Package
RJP4002ANS	V <sub>CES</sub> = 400V(max), I <sub>CP</sub> = 150A(max), 2.5V drive	VSON-8
RJP4002ASA	V <sub>CES</sub> = 400V(max), I <sub>CP</sub> = 150A(max), 2.5V drive	TSSOP-8
RJP4003ANS	V <sub>CES</sub> = 400V(max), I <sub>CP</sub> = 150A(max), 4V drive	VSON-8
RJP4003ASA	V <sub>CES</sub> = 400V(max), I <sub>CP</sub> = 150A(max), 4V drive	TSSOP-8

## **Package Dimensions**



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